

IN THE CLAIMS:

**Please amend claims 43, 44, 50, and 51 and add new claims 58-77 as follows:**

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Claims 1-42 (previously cancelled)

43. (Currently amended) A tested semiconductor device produced by a process comprising the steps of:

providing a wafer having a plurality of semiconductor devices thereon, each of said semiconductor devices including a plurality of electrical contact ~~pads~~ terminals;

C3 providing a probe card assembly, said probe card assembly including a probe card having a plurality of electrical contacts, a probe substrate having a plurality of ~~elongate, resilient~~ probe elements, and ~~a compliant interconnection structure electrically connecting said ones of said electrical contacts with corresponding ones of said probe elements~~ an interposer disposed between said probe card and said probe substrate, said interposer allowing relative movement between said probe card and said probe substrate while maintaining electrical connections between ones of said electrical contacts and ones of said probe elements;

contacting said wafer and said probe card assembly such that ones of said electrical contact ~~pads~~ terminals of said semiconductor devices are in electrical contact with ones of said probe elements; and

testing said semiconductor devices.

44. (Currently amended) The tested semiconductor device of claim 43, wherein said process further comprises aligning tips of said probe elements with said ~~corresponding~~ electrical contact ~~pads~~ terminals.

45. (Previously added) The tested semiconductor device of claim 44, wherein said aligning tips of said probe elements includes altering an orientation of said probe substrate with respect to said probe card.

46. (Previously added) The tested semiconductor device of claim 45, wherein said altering comprises moving a moveable element disposed so as to affect an orientation of said probe substrate with respect to said probe card.

47. (Previously added) The tested semiconductor device of claim 44, wherein said aligning further comprises aligning said tips with an alignment plate.

C2 48. (Previously added) The tested semiconductor device of claim 43, wherein the process further comprises dicing said wafer to singulate said semiconductor devices.

49. (Previously added) The tested semiconductor device of claim 43, wherein said probe substrate comprises a space transformer.

50. (Currently amended) A tested semiconductor device produced by a process comprising the steps of:

providing a probe card comprising a plurality of electrical contacts;

providing a probe substrate ~~moveably fixed~~ mounted to said probe card and comprising a plurality of ~~elongate, resilient~~ probe elements, ones of said ~~elongate resilient~~ probe elements being in electrical communication with ones of said electrical contacts;

aligning tips of said probe elements by altering an orientation of said probe substrate with respect to said probe card, said altering comprising moving a moveable element disposed so as to affect an orientation of said probe substrate with respect to said probe card;

providing a semiconductor device;

bringing said tips into contact with said semiconductor device; and

testing said semiconductor device.

51. (Currently amended) The tested semiconductor device of claim 50, wherein said moveable element ~~is~~ comprises a threaded element.

52. (Previously added) The tested semiconductor device of claim 50, wherein said moveable element comprises a screw.

53. (Previously added) The tested semiconductor device of claim 52, wherein said screw comprises a differential screw.

54. (Previously added) The tested semiconductor device of claim 50, wherein moving said moveable element in a first direction causes at least a portion of said probe substrate to move toward said probe card.

55. (Previously added) The tested semiconductor device of claim 54, wherein moving said moveable element in a second direction allows at least a portion of said probe substrate to move away from said probe card.

C3 56. (Previously added) The tested semiconductor device of claim 50, wherein said altering comprises actuating a servo mechanism disposed to alter a position of said probe substrate with respect to said probe card.

57. (Previously added) The tested semiconductor device of claim 50, wherein said altering comprises actuating a piezoelectric actuator disposed to alter a position of said probe substrate with respect to said probe card.

58. (New) The tested semiconductor device of claim 43, wherein said interposer comprises flexible contact structures electrically connecting said ones of said electrical contacts with said ones of said probe elements.

59. (New) The tested semiconductor device of claim 43, wherein said probe elements are elongate and resilient.

60. (New) The tested semiconductor device of claim 44, wherein said step of aligning tips of said probe elements further comprises planarizing said tips with respect to said electrical contact terminals of said semiconductor device.

61. (New) The tested semiconductor device of claim 46, wherein said moveable element comprises a pivot structure.
62. (New) The tested semiconductor device of claim 61, wherein said pivot structure is disposed against said probe substrate.
63. (New) The tested semiconductor device of claim 46, wherein said moveable element comprises a sphere.
64. (New) The tested semiconductor device of claim 46, wherein said moveable element comprises a differential screw that comprises an outer threaded portion and an inner threaded portion.
65. (New) The tested semiconductor device of claim 50, wherein said probe substrate is mounted to said probe card by a means that is different than said moveable element.
66. (New) The tested semiconductor device of claim 50, wherein said probe elements are elongate and resilient.
67. (New) The tested semiconductor device of claim 50, wherein said step of aligning tips of said probe elements comprises planarizing said tips.
68. (New) The tested semiconductor device of claim 67, wherein said step of aligning tips of said probe elements further comprises planarizing said tips with respect to said semiconductor device.
69. (New) The tested semiconductor device of claim 50, wherein said moveable element comprises a pivot structure.
70. (New) The tested semiconductor device of claim 69, wherein said pivot structure is disposed against said probe substrate.

71. (New) The tested semiconductor device of claim 50, wherein said moveable element comprises a sphere.

72. (New) The tested semiconductor device of claim 53, wherein said differential screw comprises an outer threaded portion and an inner threaded portion.

73. (New) The tested semiconductor device of claim 50, wherein said probe substrate is floatingly mounted to said probe card.

*C3  
Conclude*

74. (New) The tested semiconductor device of claim 50 wherein:  
said probe substrate is mounted to said probe card with a biasing force, and  
said moveable element is configured to apply a force in opposition to said biasing force.

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